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cont

[illegible]

18. [(New)] The electroplating process unit of Claim 17 wherein said annular recirculation inlet has a first diameter that is smaller than a second diameter of said annular waste inlet.

- positioning a wafer in said wafer holder;
- introducing a plating solution into said plating bath container;
- immersing said wafer in said plating solution;
- using said actuator to move said wafer holder to a first position above said solution;

using said actuator to move said wafer holder to a second position above said solution; and

20. [(New)] The method of Claim 19 wherein said first volume of rinse solution is smaller than said second volume of rinse solution.

a plating bath container;

a wafer holder;

an actuator coupled to said wafer holder, said actuator being capable of rotating said wafer holder about a vertical axis and of moving said wafer holder upward and downward along said vertical axis; and

an annular waste inlet located at a level above said plating bath container, said annular waste inlet being in flow communication with a waste drain;
said method comprising:

positioning a wafer in said wafer holder;

introducing a plating solution into said plating bath container;

using said actuator to move said wafer holder to a first position above said plating solution;

while said wafer is in said first position, pre-wetting said wafer by spraying a first volume of rinse solution against said wafer and rotating said wafer at a rate such that substantially all of said first volume of rinse solution enters said annular waste inlet; and

after said pre-wetting, immersing said wafer in said plating solution.

22. (New) The method of Claim 21 wherein said electroplating unit further comprises an annular recirculation inlet located at a second level above said plating bath container, said annular recirculation inlet being in flow communication with a pump for recirculating a fluid to said plating bath container, said method comprising:

after said immersing, using said actuator to move said wafer holder to a second position above said plating solution; and

while said wafer is in said second position, spraying a second volume of rinse solution against said wafer while and rotating said wafer at a rate such that substantially all of said second volume of rinse solution enters said annular recirculation inlet.

23. (New) The method of Claim 22 comprising:

after said spraying said second volume of rinse solution, using said actuator to move said wafer holder to said first position; and